

EconoPACK™3 module with Trench/Fieldstop IGBT4 and emitter controlled 4 diode

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{ nom}} = 25\text{ A} / I_{CRM} = 50\text{ A}$
 - Low switching losses
 - Low $V_{CE,sat}$
 - Trench IGBT 4
 - $T_{vj,op} = 150^{\circ}\text{C}$
 - $V_{CE,sat}$ with positive temperature coefficient
- Mechanical features
 - Al_2O_3 substrate with low thermal resistance
 - High power and thermal cycling capability
 - Integrated NTC temperature sensor
 - Copper base plate
 - Solder contact technology
 - RoHS compliant
 - Standard housing



Potential applications

- Auxiliary inverters
- Motor drives
- Servo drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

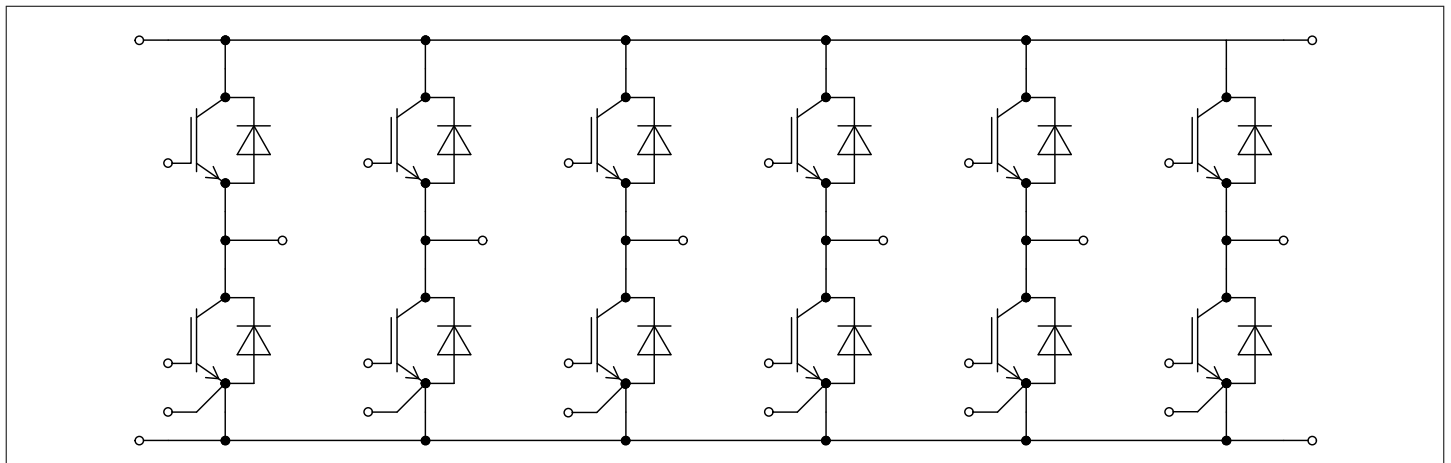


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1 Package

1 Package

Table 1 **Insulation coordination**

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	CTI		> 200	

Table 2 **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, case to heat sink	R_{thCH}	$\lambda_{grease} = 1 \text{ W/(m}\cdot\text{K)}$		0.009		K/W
Stray inductance module	L_{sCE}			20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25 \text{ }^\circ\text{C}$, per switch		2.5		mΩ
Storage temperature	T_{stg}		-40		125	$^\circ\text{C}$
Mounting torque for module mounting	M	- Mounting according to valid application note	3		6	Nm
Weight	G			300		g

2 IGBT, Inverter

Table 3 **Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25 \text{ }^\circ\text{C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175 \text{ }^\circ\text{C}$ $T_C = 100 \text{ }^\circ\text{C}$	25	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj \text{ op}}$	50	A
Gate-emitter peak voltage	V_{GES}		± 20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 25\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.85	2.15	V
			$T_{vj} = 125\ ^\circ C$		2.15		
			$T_{vj} = 150\ ^\circ C$		2.25		
Gate threshold voltage	V_{GETh}	$I_C = 0.8\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.20	5.80	6.40	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V$			0.2		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			0		Ω
Input capacitance	C_{ies}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			1.45		nF
Reverse transfer capacitance	C_{res}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.05		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			1	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 20\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.030		μs
			$T_{vj} = 125\ ^\circ C$		0.030		
			$T_{vj} = 150\ ^\circ C$		0.030		
Rise time (inductive load)	t_r	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 20\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.020		μs
			$T_{vj} = 125\ ^\circ C$		0.025		
			$T_{vj} = 150\ ^\circ C$		0.025		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 20\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.180		μs
			$T_{vj} = 125\ ^\circ C$		0.270		
			$T_{vj} = 150\ ^\circ C$		0.290		
Fall time (inductive load)	t_f	$I_C = 25\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 20\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.160		μs
			$T_{vj} = 125\ ^\circ C$		0.170		
			$T_{vj} = 150\ ^\circ C$		0.180		
Turn-on energy loss per pulse	E_{on}	$I_C = 25\ A, V_{CC} = 600\ V, L_\sigma = 20\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 20\ \Omega, di/dt = 1300\ A/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		1.7		mJ
			$T_{vj} = 125\ ^\circ C$		2.3		
			$T_{vj} = 150\ ^\circ C$		2.4		
Turn-off energy loss per pulse	E_{off}	$I_C = 25\ A, V_{CC} = 600\ V, L_\sigma = 20\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 20\ \Omega, dv/dt = 4000\ V/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		1.4		mJ
			$T_{vj} = 125\ ^\circ C$		2		
			$T_{vj} = 150\ ^\circ C$		2.15		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 800\ V, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_P \leq 10\ \mu s, T_{vj} = 150\ ^\circ C$		90		A

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.950	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W/(m}\cdot\text{K)}$		0.185		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		150	°C

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25 \text{ °C}$	1200	V
Continuous DC forward current	I_F			25	A
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$		70	A
I^2t - value	I^2t	$t_P = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ °C}$	90	A^2s
			$T_{vj} = 150 \text{ °C}$	80	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 25 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$	1.75	2.15	V
			$T_{vj} = 125 \text{ °C}$	1.75		
			$T_{vj} = 150 \text{ °C}$	1.75		
Peak reverse recovery current	I_{RM}	$V_{CC} = 600 \text{ V}, I_F = 25 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1300 \text{ A/}\mu\text{s} (T_{vj} = 150 \text{ °C})$	$T_{vj} = 25 \text{ °C}$	39		A
			$T_{vj} = 125 \text{ °C}$	40		
			$T_{vj} = 150 \text{ °C}$	41		
Recovered charge	Q_r	$V_{CC} = 600 \text{ V}, I_F = 25 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1300 \text{ A/}\mu\text{s} (T_{vj} = 150 \text{ °C})$	$T_{vj} = 25 \text{ °C}$	2.5		μC
			$T_{vj} = 125 \text{ °C}$	4.2		
			$T_{vj} = 150 \text{ °C}$	4.9		
Reverse recovery energy	E_{rec}	$V_{CC} = 600 \text{ V}, I_F = 25 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 1300 \text{ A/}\mu\text{s} (T_{vj} = 150 \text{ °C})$	$T_{vj} = 25 \text{ °C}$	0.9		mJ
			$T_{vj} = 125 \text{ °C}$	1.5		
			$T_{vj} = 150 \text{ °C}$	1.8		

(table continues...)

Table 6 (continued) Characteristic values

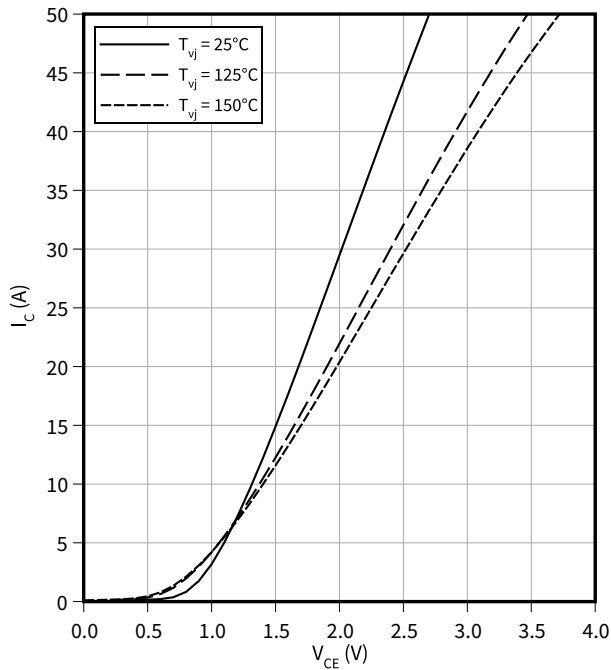
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance, junction to case	R_{thJC}	per diode			1.35	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W/(m}\cdot\text{K)}$		0.260		K/W
Temperature under switching conditions	T_{vjop}		-40		150	°C

4 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

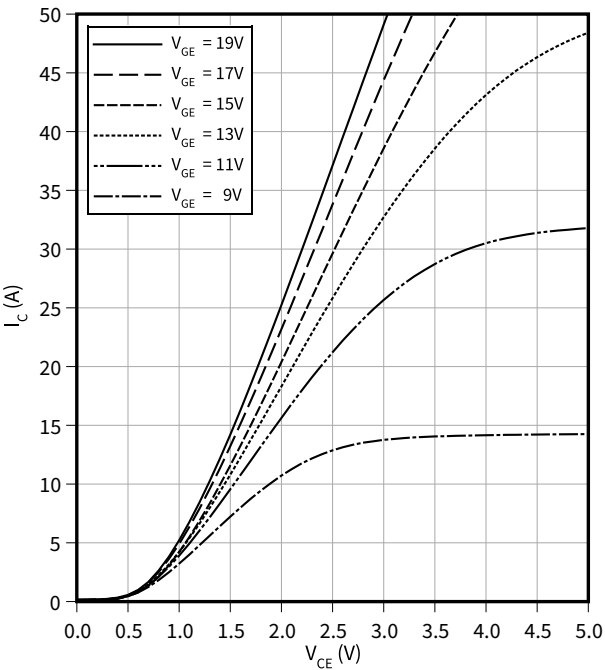
$V_{GE} = 15\text{ V}$



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

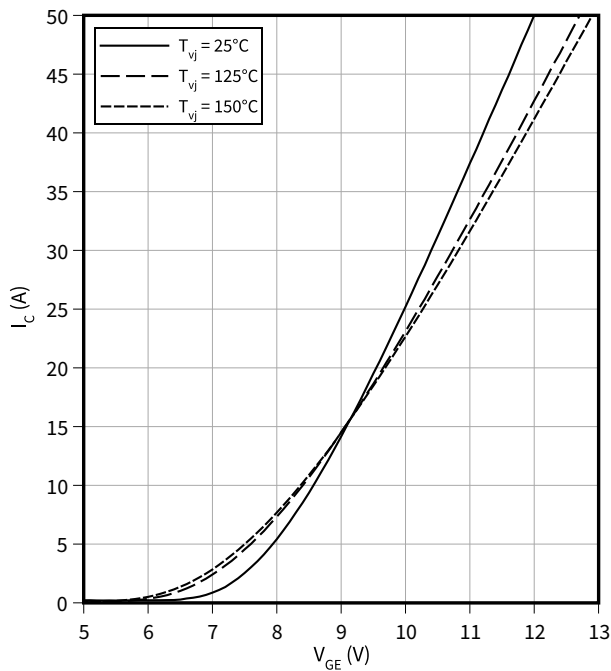
$T_{vj} = 150^\circ\text{C}$



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

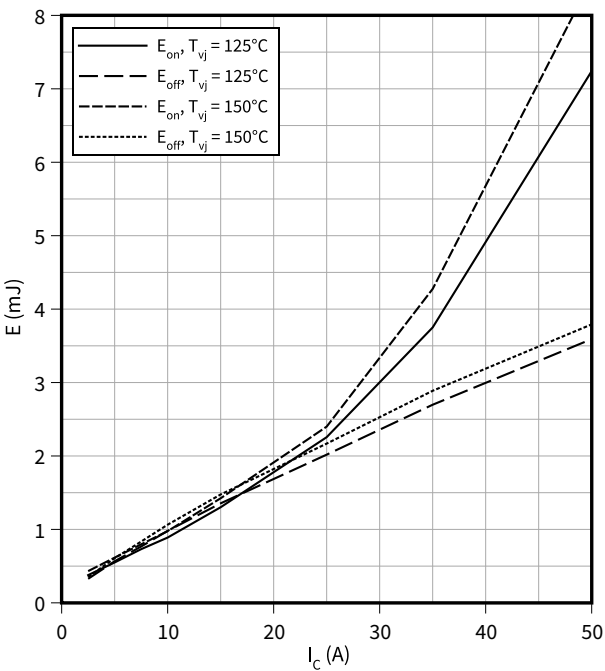
$V_{CE} = 20\text{ V}$



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

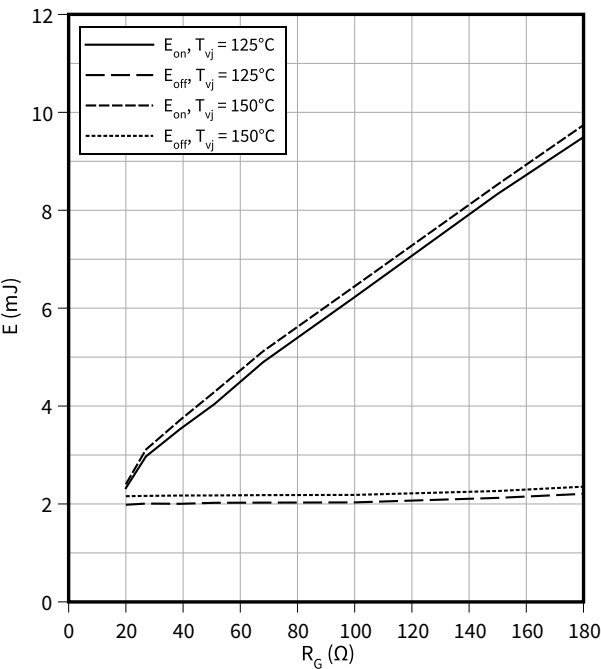
$R_{Goff} = 20\ \Omega$, $R_{Gon} = 20\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $V_{CC} = 600\text{ V}$



4 Characteristics diagrams

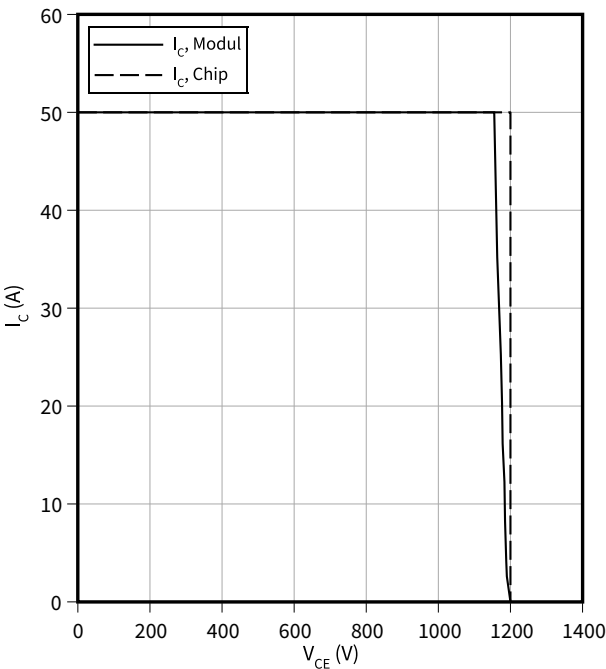
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 25\text{ A}$, $V_{CC} = 600\text{ V}$



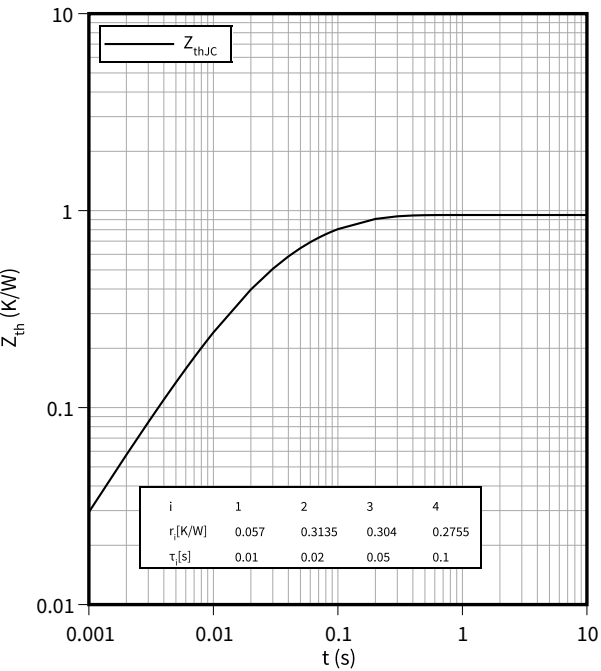
Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$
 $R_{Goff} = 20\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 150^\circ\text{C}$



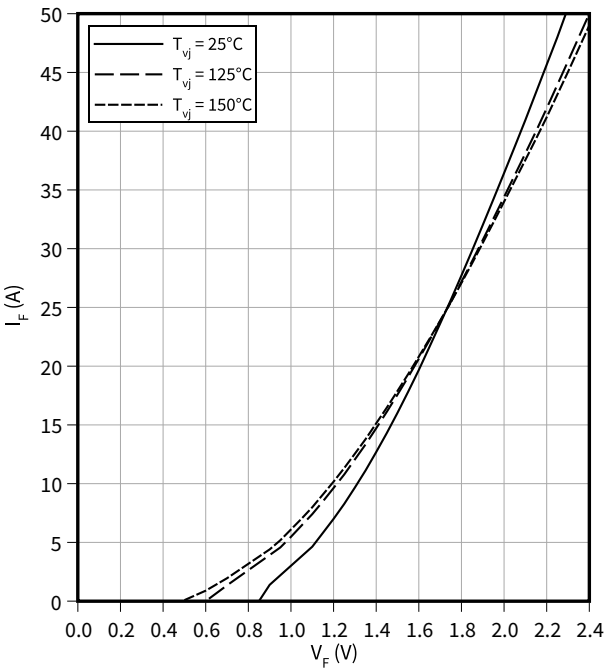
Transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Inverter

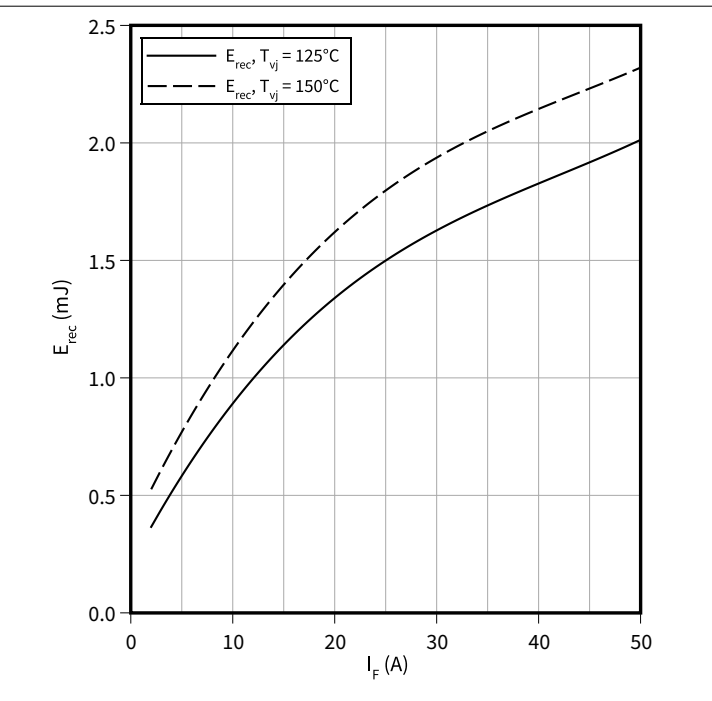
$I_F = f(V_F)$



4 Characteristics diagrams

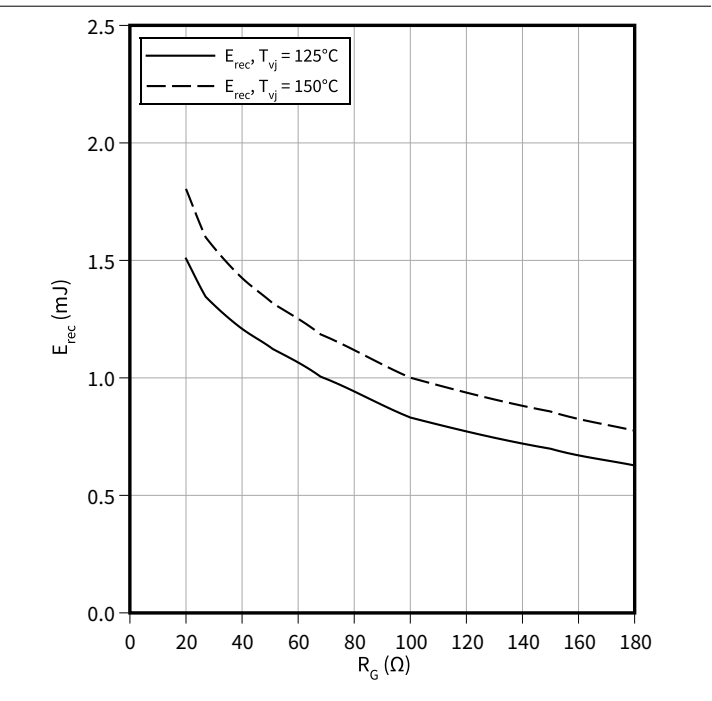
Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$
 $R_{Gon} = R_{Gon}(IGBT) , V_{CC} = 600 V$



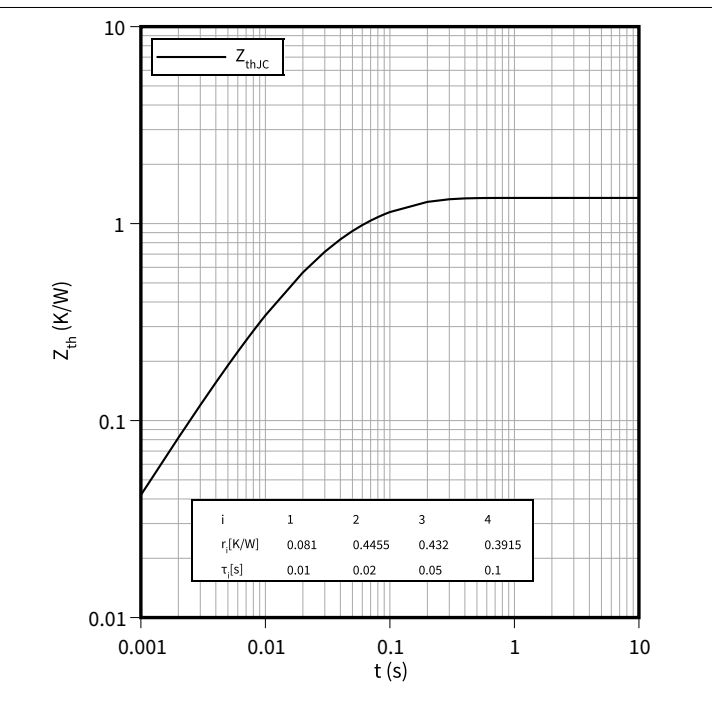
Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $I_F = 25 A, V_{CC} = 600 V$



Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



5 Circuit diagram

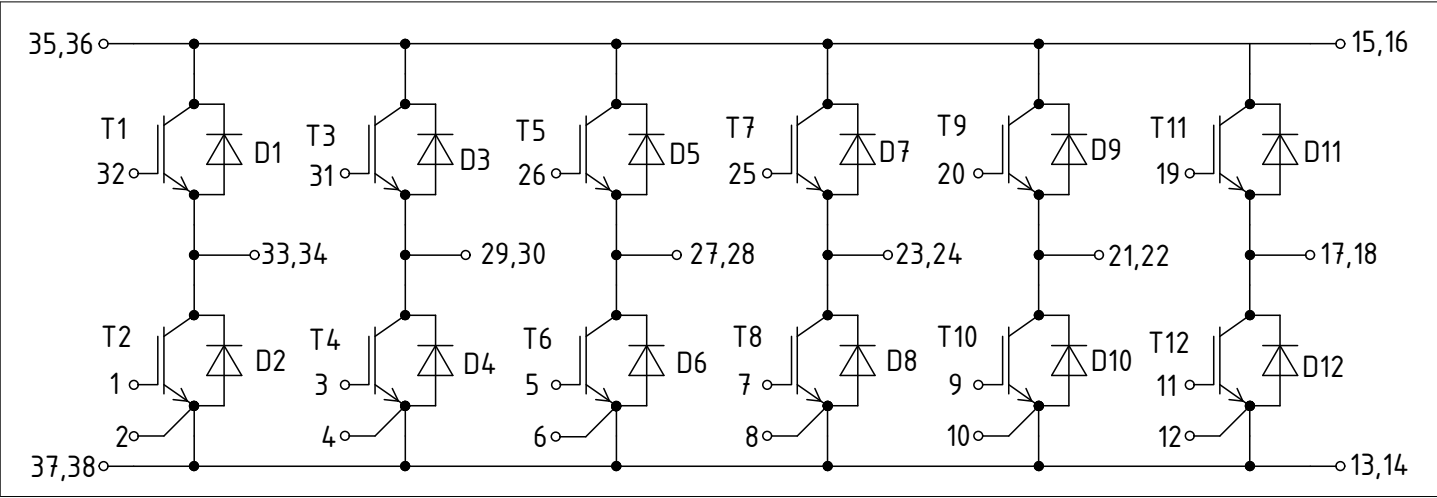


Figure 1

7 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	Content	Digit	Example
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example	 7154914284655054991153071549142846550549911530		

Figure 3

Revision history

Revision history

Document revision	Date of release	Description of changes
V1.0	2008-04-29	Target datasheet
V1.1	2008-07-29	Target datasheet
V1.2	2008-09-26	Target datasheet
V2.0	2009-02-09	Preliminary datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.00	2024-10-07	Final datasheet

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Email: erratum@infineon.com

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